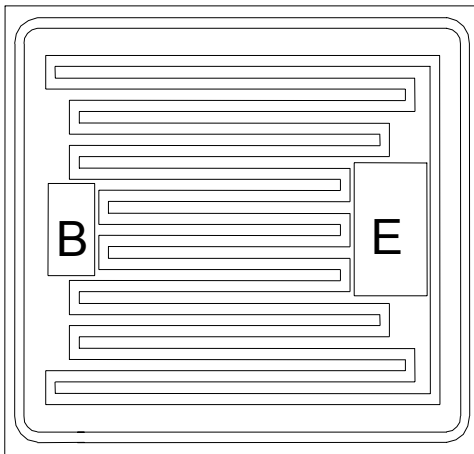


PROCESS DETAILS

PROCESS	EPITAXIAL BASE
DIE SIZE	80 x 80 MILS
DIE THICKNESS	12 MILS
BASE BONDING PAD AREA	12 x 18 MILS
EMITTER BONDING PAD AREA	13 x 28 MILS
TOP SIDE METALIZATION	Al - 30,000Å
BACK SIDE METALIZATION	Cr/Ni/Ag - Ni-6,000Å; Ag-10,000Å

GEOMETRY



BACKSIDE COLLECTOR

PRINCIPAL DEVICE TYPES

CJD42C

TIP42C

Please refer to
selection guide on page 20.